

RB717F SCHOTTKY BARRIER DIODE

FEATURES:

Power dissipation

P_D : 200 mW ($T_{amb}=25^\circ\text{C}$)

Collector current

I_F : 30 mA

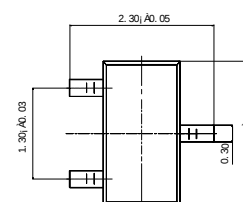
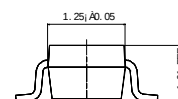
Collector-base voltage

V_R : 40 V

Operating and storage junction temperature range

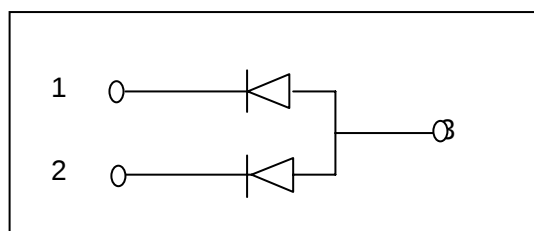
T_J, T_{stg} : -55°C to $+150^\circ\text{C}$

SOT-323



Unit: mm

CIRCUIT:



MARKING: 3E

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	40		V
Reverse voltage leakage current	I_R	$V_R=10\text{V}$		1	μA
Forward voltage	V_F	$I_F=1\text{mA}$		0.37	V
Diode capacitance	C_D	$V_R=1\text{V}, f=1\text{MHz}$		5	pF